

WHAT IS CLAIMED IS:

1 1. An applying method for an adhesive, which is provided to apply an
2 adhesive on a SiO₂ layer of a wafer placed in an closed container, wherein the closed
3 container is connected with a transmission pipeline by a supply vent, wherein the
4 transmission pipeline is used for conveying the adhesive to the closed container, wherein the
5 closed container also includes an exhaust vent, wherein the exhaust vent is externally
6 connected with a first exhaust pipe and a second exhaust pipe, and wherein the applying
7 method comprising:

8 (a) exhausting gas from the first exhaust pipe, so as to eliminate a part of the
9 gas in the closed container;

10 (b) continuing to exhaust the gas from the first exhaust pipe so as to cause
11 bubbling of the adhesive in the transmission pipeline and convey bubbled adhesive to the
12 supply vent;

13 (c) exhausting the gas from the second exhaust pipe and continuing to exhaust
14 the gas from the first exhaust pipe so as to greatly increase exhaust of the gas in the closed
15 container and increase bubbling of the adhesive; and

16 (d) continuing to exhaust the gas from the second exhaust pipe and ceasing
17 exhausting the gas from the first exhaust pipe so as to have the adhesive reach a gasification
18 state, wherein the gasified adhesive is supplied to the closed container from the supply vent,
19 and wherein the gasified adhesive is adhered and coated on the SiO₂ layer.

1 2. The applying method as recited in claim 1, wherein operation time of
2 the step (a) is approximately five seconds.

1 3. The applying method as recited in claim 1, wherein operation time of
2 the step (b) is approximately five seconds.

1 4. The applying method as recited in claim 1, wherein operation time of
2 the step (c) is approximately five seconds.

1 5. The applying method as recited in claim 1, wherein operation time of
2 the step (d) is approximately forty seconds.

1 6. The applying method as recited in claim 1, further comprising:

2 (e) exhausting the gas from the first exhaust pipe and ceasing exhausting the
3 gas from the second exhaust pipe, wherein the remaining gasified adhesive in the closed
4 container is pumped out, and wherein operation time of the step (e) is approximately seven
5 seconds.

1 7. The applying method as recited in claim 1, wherein the first exhaust
2 pipe is connected to a pump, and the second exhaust pipe is connected to a gas-extracting
3 pipe.

1 8. The applying method as recited in claim 1, wherein a gas-extracting
2 flow rate of the first exhaust pipe is greater than a gas-extracting flow rate of the second
3 exhaust pipe.

1 9. The applying method as recited in claim 1, wherein the adhesive is
2 coated on the SiO₂ layer prior to applying a photoresist on the SiO₂ layer.

1 10. The applying method as recited in claim 9, wherein the adhesive is
2 coated on the SiO₂ layer to adhere the photoresist on the SiO₂ layer.

1 11. The applying method as recited in claim 1, wherein the adhesive
2 comprises hexamethyldisilazane (HMDS).

1 12. The applying method as recited in claim 1, which is provided in micro-
2 fabrication of devices including devices selected from the group consisting of a liquid crystal
3 display driver (LCD Driver), a power integrated circuit (Power IC), and a mask read only
4 memory (Mask ROM).

1 13. A method of applying an adhesive on a wafer, the method comprising:
2 (a) placing the wafer in a closed container having a transmission line
3 connected to an inlet of the closed container to supply the adhesive to the closed container,
4 and a first exhaust line and a second exhaust line connected to an outlet of the closed
5 container;
6 (b) bubbling the adhesive in the transmission line by exhausting a portion of
7 gas from the closed container via the first exhaust line;

(c) enhancing bubbling of the adhesive in the transmission line by exhausting the gas from the closed container via the second exhaust line and continuing to exhaust the gas from the closed container via the first exhaust line; and

(d) gasifying the adhesive in the transmission line and flowing the gasified adhesive into the closed container via the inlet to adhere to and coat the wafer by continuing to exhaust the gas from the closed container via the second exhaust line and ceasing exhausting the gas from the closed container via the first exhaust line.

14. The method as recited in claim 13, wherein a gas-extracting flow rate of the first exhaust line is greater than a gas-extracting flow rate of the second exhaust line.

15. The method as recited in claim 13, wherein the first exhaust line is connected to a pump, and the second exhaust line is connected to a gas-extracting line without a pump.

16. The method as recited in claim 13, wherein the adhesive is coated on a SiO₂ layer on the wafer prior to applying a photoresist on the SiO₂ layer.

17. The method as recited in claim 16, wherein the adhesive is coated on the SiO_2 layer to adhere the photoresist onto the SiO_2 layer.

18. The method as recited in claim 13, wherein the adhesive comprises hexamethyldisilazane (HMDS).

19. The method as recited in claim 13, further comprising:

(e) removing remaining gasified adhesive in the closed container by exhausting the gas from the closed container via the first exhaust line while ceasing exhausting the gas from the closed container via the second exhaust line.

20. The method as recited in claim 19, wherein the operation time of the step (b) is about ten seconds, the operation time of the step (c) is about five seconds, the operation time of the step (d) is about forty seconds, and the operation time of the step (e) is about seven seconds.

21. A method of applying an adhesive on a wafer, the method comprising:
(a) placing the wafer in a closed container having a transmission line
connected to an inlet of the closed container to supply the adhesive to the closed container,

4 and a first exhaust line and a second exhaust line connected to an outlet of the closed
5 container, the first exhaust line being coupled to a pump to pump from the closed container,
6 the second exhaust line having no pump coupled thereto;

7 (b) bubbling the adhesive in the transmission line by pumping gas from the
8 closed container via the first exhaust line;

9 (c) enhancing bubbling of the adhesive in the transmission line by exhausting
10 the gas from the closed container via the second exhaust line and continuing to pump the gas
11 from the closed container via the first exhaust line; and

12 (d) gasifying the adhesive in the transmission line and flowing the gasified
13 adhesive into the closed container via the inlet to adhere to and coat the wafer by continuing
14 to exhaust the gas from the closed container via the second exhaust line and ceasing pumping
15 the gas from the closed container via the first exhaust line.

1 22. The method of claim 21, further comprising:

2 (e) removing remaining gasified adhesive in the closed container by pumping
3 the gas from the closed container via the first exhaust line while ceasing exhausting the gas
4 from the closed container via the second exhaust line.

1 23. The method as recited in claim 21, wherein the adhesive is coated on a
2 SiO₂ layer on the wafer prior to applying a photoresist on the SiO₂ layer to adhere the
3 photoresist onto the SiO₂ layer.